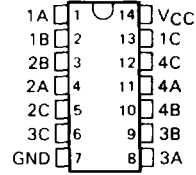


SN54HC4016, TLC4016I SILICON-GATE CMOS QUADRUPLE BILATERAL ANALOG SWITCH

D2922, JANUARY 1986

- High Degree of Linearity
- High On-Off Output Voltage Ratio
- Low Crosstalk Between Switches
- Low On-State Impedance of 50 Ohms Typ at $V_{CC} = 9\text{ V}$
- Individual Switch Controls
- Extremely Low Input Current

SN54HC4016 . . . J OR N PACKAGE
TLC4016I . . . D OR N PACKAGE
(TOP VIEW)



description

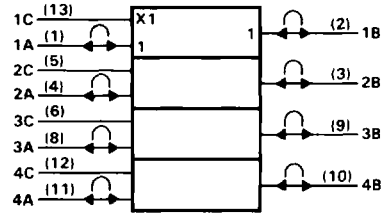
The TLC4016 is a silicon-gate CMOS quadruple analog switch integrated circuit designed to handle both analog and digital signals. Each switch permits signals with amplitudes up to 12 volts peak to be transmitted in either direction.

Each switch section has its own enable input control. A high-level voltage applied to this control terminal turns on the associated switch section.

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.

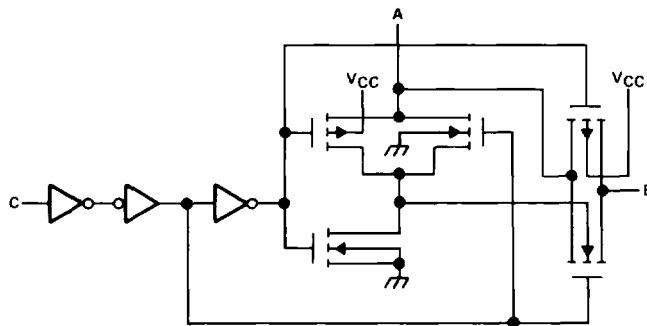
The SN54HC4016 is characterized for operation from -55°C to 125°C , and the TLC4016I is characterized from -40°C to 85°C .

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



PRODUCTION DATA documents contain information current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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SN54HC4016, TLC4016I
SILICON-GATE CMOS QUADRUPLE BILATERAL ANALOG SWITCH

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted).

PARAMETER	TEST CONDITIONS	V _{CC}	SN54HC4016			TLC4016I			UNIT
			MIN	TYP [†]	MAX	MIN	TYP [†]	MAX	
I _{SON} On state switch resistance	I _S = 1 mA, V _A = 0 to V _{CC} , See Figure 1	4.5 V	100	220	100	200	Ω		
		9 V	50	120	50	105			
		12 V	30	100	30	85			
	I _S = 1 mA, V _A = 0 or V _{CC} , See Figure 1	2 V	120	240	120	215			
		4.5 V	50	120	50	100			
		9 V	35	80	35	75			
On state switch resistance matching	V _A = 0 to V _{CC} , See Figure 1	4.5 V	10	20	10	20	Ω		
		9 V	5	15	5	15			
		12 V	5	15	5	15			
I _I Control input current	V _I = 0 or V _{CC} , T _A = 25°C	2 V		+1		±1	μA		
		to							
		6 V		+0.1		±0.1			
I _{SOFF} Off state switch leakage current	V _S = +V _{CC} , See Figure 2	5.5 V	+10	+600	+10	+600	nA		
		9 V	+15	+800	+15	+800			
		12 V	+20	+1000	+20	+1000			
I _{SON} On state switch leakage current	V _A = 0 or V _{CC} , See Figure 3	5.5 V	+10	+150	+10	+150	nA		
		9 V	+15	+200	+15	+200			
		12 V	+20	+300	+20	+300			
I _{CC} Supply current	V _I = 0 or V _{CC} , I _O = 0	5.5 V	2	40	2	20	μA		
		9 V	8	160	8	80			
		12 V	16	320	16	160			
C _i Input capacitance	A or B C	2 V to	15		15		pF		
		12 V	5 10		5 10				
C _f Feedthrough capacitance	A to B	2 V to	5		5		pF		
		12 V							

[†]All typical values are at T_A = 25°C.

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HC MOS Devices

SN54HC4016, TLC4016 SILICON-GATE CMOS QUADRUPLE BILATERAL ANALOG SWITCH

switching characteristics over recommended operating free-air temperature range, $C_L = 50$ pF (unless otherwise noted)

PARAMETER	TEST CONDITIONS	VCC	SN54HC4016			TLC4016I			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
t_{pd} Propagation delay time, A to B or B to A	See Figure 4	2 V		25	75	25	62	ns	
		4.5 V		5	15	5	13		
		9 V		4	14	4	12		
		12 V		3	13	3	11		
t_{on} Switch turn-on time	$R_L = 1$ k Ω . See Figures 5 and 6	2 V		32	150	32	125	ns	
		4.5 V		8	30	8	25		
		9 V		6	18	6	15		
		12 V		5	15	5	13		
t_{off} Switch turn-off time	$R_L = 1$ k Ω . See Figures 5 and 6	2 V		45	252	45	210	ns	
		4.5 V		15	54	15	45		
		9 V		10	48	10	40		
		12 V		8	45	8*	38		
f_{co} Switch cutoff frequency (channel loss = 3 dB)		4.5 V		100		100	MHz		
		9 V		120		120			
$V_{OCF(PP)}$ Control feedthrough voltage to any switch, peak to peak	See Figure 7	4.5 V		180		180	mV		
Frequency at which crosstalk attenuation between any two switches equals 50 dB	See Figure 8	4.5 V		1		1	MHz		

† All typical values are at $T_A = 25^\circ\text{C}$.

PARAMETER MEASUREMENT INFORMATION

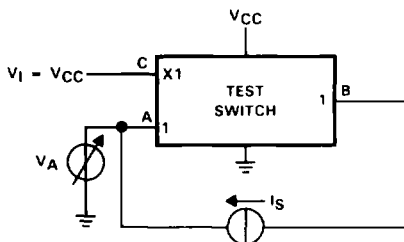
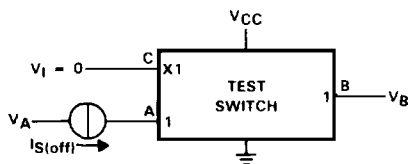


FIGURE 1. ON-STATE RESISTANCE TEST CIRCUIT



$$V_S = V_A - V_B$$

CONDITION 1: $V_A = 0$, $V_B = V_{CC}$

CONDITION 2: $V_A = V_{CC}$, $V_B = 0$

FIGURE 2. OFF-STATE SWITCH LEAKAGE CURRENT TEST CIRCUIT

PARAMETER MEASUREMENT INFORMATION

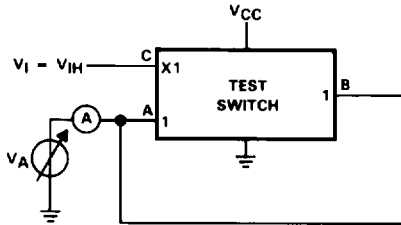


FIGURE 3. ON-STATE SWITCH LEAKAGE CURRENT TEST CIRCUIT

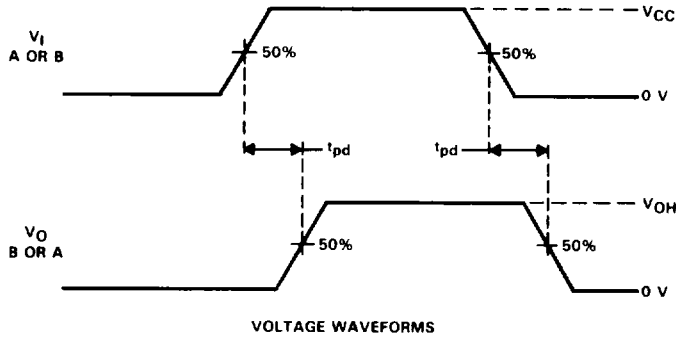
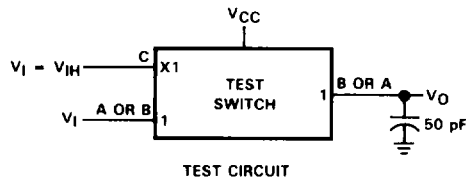
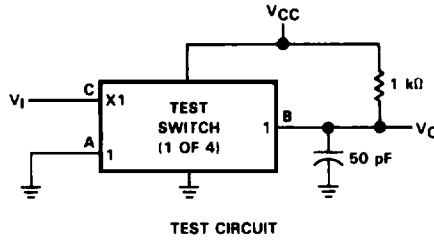


FIGURE 4. PROPAGATION DELAY TIME, SIGNAL INPUT TO SIGNAL OUTPUT

SN54HC4016, TLC4016I
SILICON-GATE CMOS QUADRUPLE BILATERAL ANALOG SWITCH

PARAMETER MEASUREMENT INFORMATION



2

HC MOS Devices

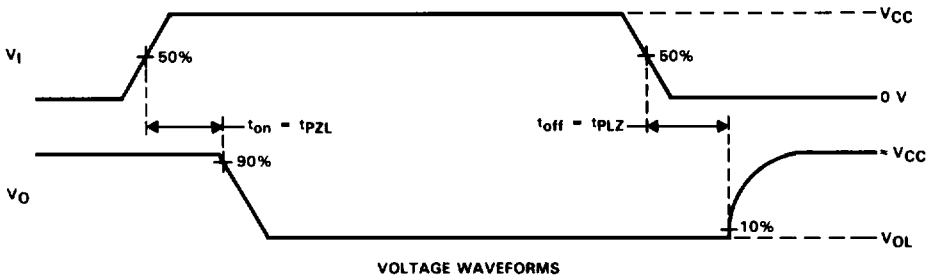


FIGURE 5. SWITCHING TIME (t_{PZL} , t_{PLZ}), CONTROL TO SIGNAL OUTPUT

PARAMETER MEASUREMENT INFORMATION

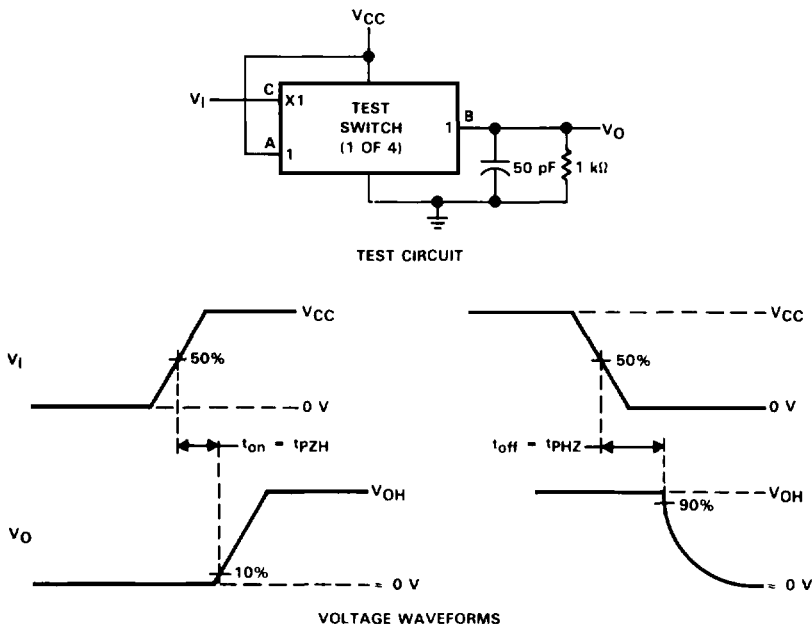


FIGURE 6. SWITCHING TIME (t_{pZH} , t_{pHZ}), CONTROL TO SIGNAL OUTPUT

PARAMETER MEASUREMENT INFORMATION

2

HCMOS Devices

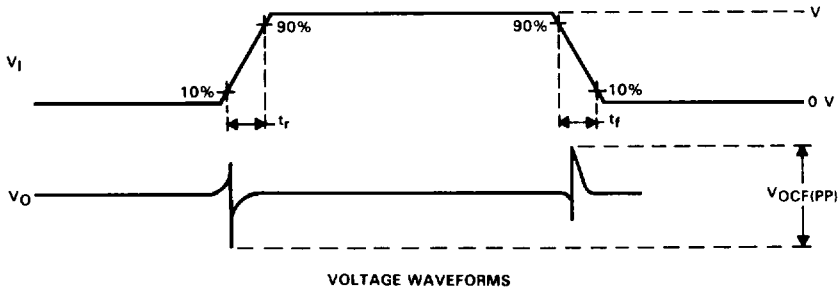
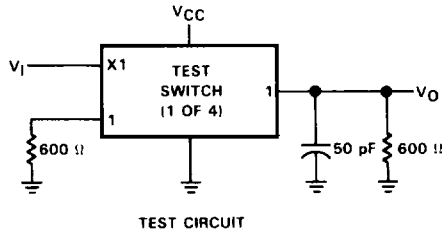
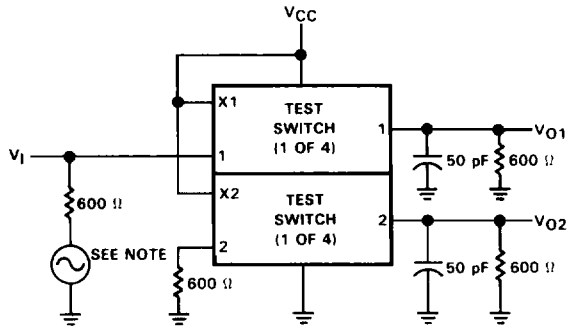


FIGURE 7. CONTROL FEEDTHROUGH VOLTAGE



NOTE: ADJUST f for $a_X = \frac{V_{O2}}{V_{O1}} = 50 \text{ dB}$.

FIGURE 8. CROSSTALK BETWEEN ANY TWO SWITCHES, TEST CIRCUIT